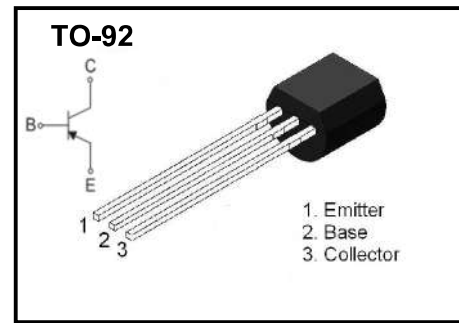


**PNP Plastic-Encapsulate Transistors  
Darlington Transistor**
**FEATURES**

- ♦ High current gain
- ♦ High collector current
- ♦ Complementary type: BC517

Marking Code	
BC516	YFW BC516


**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$BV_{CBO}$	-40	V
Collector-Emitter Voltage	$BV_{CEO}$	-30	V
Emitter-Base Voltage	$BV_{EBO}$	-10	V
Collector Current	$I_C$	-1.0	A
Collector Power Dissipation	$P_C$	0.625	W
Junction Temperature	$T_j$	-55 ~ +150	°C
Storage Temperature	$T_{stg}$	-55 ~ +150	°C

**Electrical Characteristics (Ta=25°C)**

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	$BV_{CBO}$	$I_C = -10\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$BV_{CES}$	$I_C = -2mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$BV_{EBO}$	$I_E = -100nA, I_C = 0$	-10			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -30V, I_E = 0$			-100	nA
Collector cut-off current	$I_{CES}$	$V_{CE} = -30V, I_E = 0$			-500	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -10V, I_C = 0$			-100	nA
DC current gain	$h_{FE}$	$V_{CE} = -2V, I_C = -20mA$	20000			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -0.1mA$			1.0	V
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE} = -5V, I_B = -10mA$			1.4	V
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$		200		MHz
Output capacitance	$C_{ob}$	$V_{CE} = -10V, f = 1MHz$		3.5		pF

Typical Characteristics

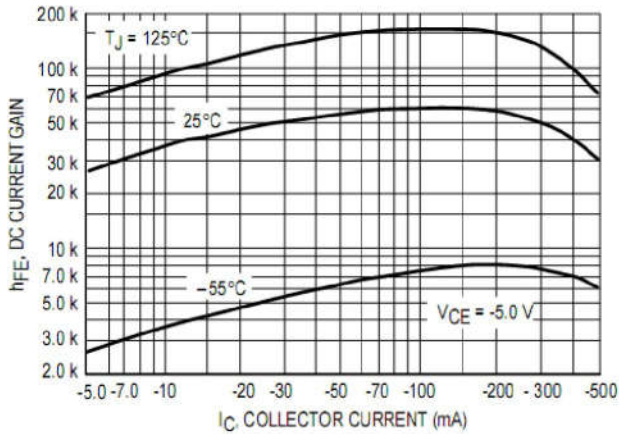


Figure 1. DC Current Gain

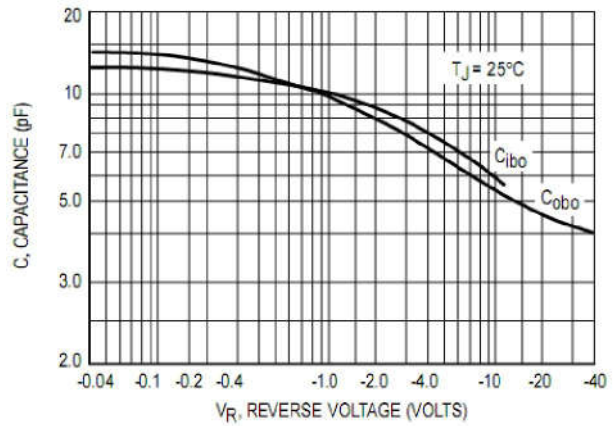


Figure 2. Capacitance

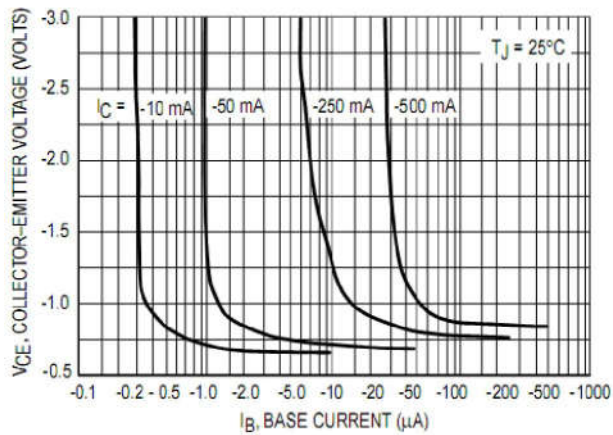


Figure 3. Collector Saturation Region

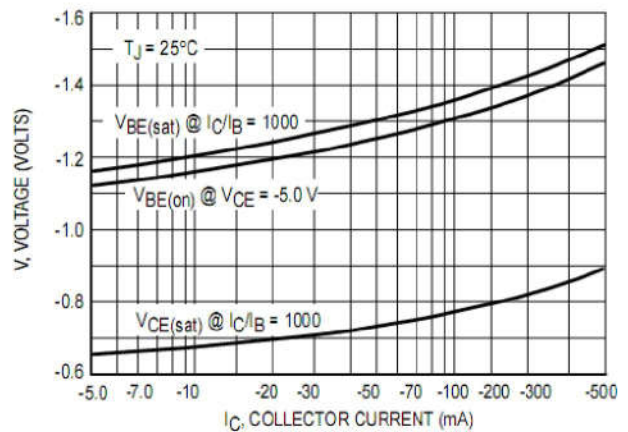


Figure 4. "On" Voltages

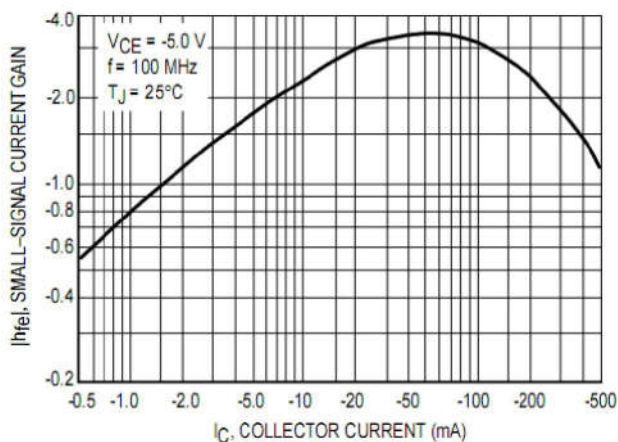


Figure 5. High Frequency Current Gain

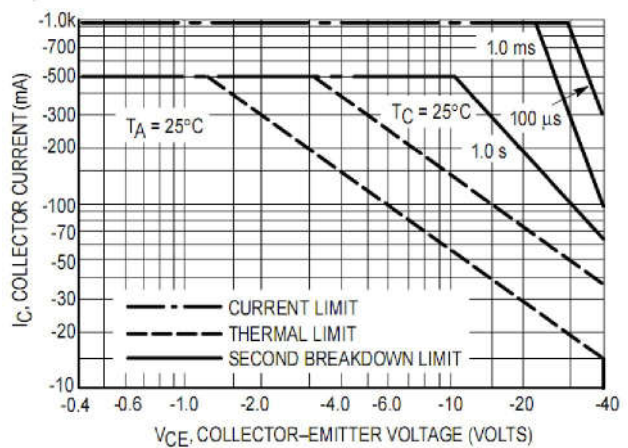


Figure 6. Active Region Safe Operating Area

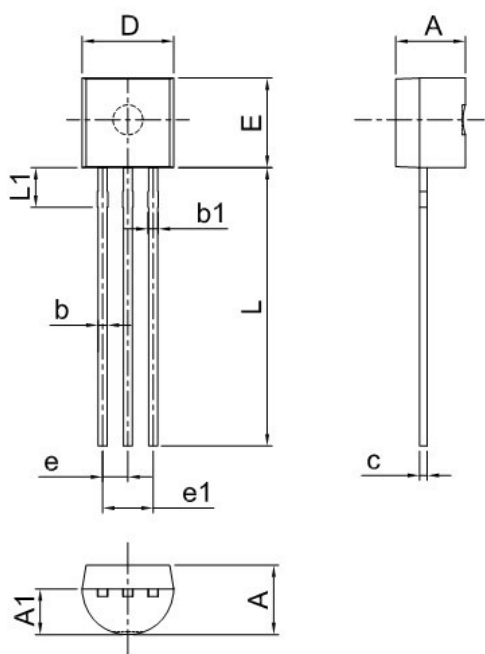
**Ordering information**

Package	Packing Description	Base Quantity
TO-92	Bulk	1000pcs/Bag
	Tape	2000pcs/Box

**Package Dimensions**

**TO-92**

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.70	0.130	0.146
A1	2.30	2.70	0.091	0.106
b	0.40	0.50	0.016	0.020
b1	0.50	0.70	0.020	0.028
c	0.35	0.45	0.014	0.018
D	4.45	4.70	0.175	0.185
E	4.40	4.65	0.173	0.183
e	1.17	1.37	0.046	0.054
e1	2.34	2.64	0.092	0.104
L	13.50	14.50	0.531	0.571
L1	1.80	2.20	0.071	0.087



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